



**Absolute Maximum Ratings**  $T_C=25^{\circ}\text{C}$  unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
$V_{CES}$	Collector-Emitter Voltage	1200	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C=25^{\circ}\text{C}$	262	A
	@ $T_C=65^{\circ}\text{C}$	200	
$I_{CM}$	Pulsed Collector Current $t_p=1\text{ms}$	400	A
$P_D$	Maximum Power Dissipation @ $T_j=150^{\circ}\text{C}$	1315	W

**Diode**

Symbol	Description	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V
$I_F$	Diode Continuous Forward Current	200	A
$I_{FM}$	Diode Maximum Forward Current $t_p=1\text{ms}$	400	A

**Module**

Symbol	Description	Value	Unit
$T_{jmax}$	Maximum Junction Temperature	150	$^{\circ}\text{C}$
$T_{jop}$	Operating Junction Temperature	-40 to +125	$^{\circ}\text{C}$
$T_{STG}$	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
$V_{ISO}$	Isolation Voltage RMS, $f=50\text{Hz}$ , $t=1\text{min}$	2500	V

**IGBT Characteristics**  $T_c=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=200\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$		3.00	3.45	V	
		$I_C=200\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$		3.80			
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=2.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$	4.5	5.4	6.5	V	
$I_{CES}$	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$			5.0	mA	
$I_{GES}$	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$			400	nA	
$R_{Gint}$	Internal Gate Resistance			1.3		$\Omega$	
$C_{ies}$	Input Capacitance			13.0		nF	
$C_{res}$	Reverse Transfer Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		0.85		nF	
$Q_G$	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		2.10		$\mu\text{C}$	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=200\text{A}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$		87		ns	
$t_r$	Rise Time			40		ns	
$t_{d(off)}$	Turn-Off Delay Time			451		ns	
$t_f$	Fall Time			63		ns	
$E_{on}$	Turn-On Switching Loss				6.8		mJ
$E_{off}$	Turn-Off Switching Loss				11.9		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=600\text{V}, I_C=200\text{A}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$		88		ns	
$t_r$	Rise Time			44		ns	
$t_{d(off)}$	Turn-Off Delay Time			483		ns	
$t_f$	Fall Time			78		ns	
$E_{on}$	Turn-On Switching Loss				11.4		mJ
$E_{off}$	Turn-Off Switching Loss				13.5		mJ
$I_{SC}$	SC Data	$t_p \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$		1300		A	

**Diode Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Diode Forward Voltage	$I_F=200\text{A}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$		1.95	2.40	V
		$I_F=200\text{A}, V_{GE}=0\text{V}, T_j=125^\circ\text{C}$		2.00		
$Q_r$	Recovered Charge	$V_R=600\text{V}, I_F=200\text{A},$ $-di/dt=4600\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^\circ\text{C}$		13.3		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current			236		A
$E_{rec}$	Reverse Recovery Energy			6.6		mJ
$Q_r$	Recovered Charge			23.0		$\mu\text{C}$
$I_{RM}$	Peak Reverse Recovery Current	$V_R=600\text{V}, I_F=200\text{A},$ $-di/dt=4600\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^\circ\text{C}$		269		A
$E_{rec}$	Reverse Recovery Energy			10.5		mJ

**Module Characteristics**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
$L_{CE}$	Stray Inductance			30	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.35		m $\Omega$
$R_{thJC}$	Junction-to-Case (per IGBT)			0.095	K/W
	Junction-to-Case (per Diode)			0.202	
$R_{thCH}$	Case-to-Heatsink (per IGBT)		0.029		K/W
	Case-to-Heatsink (per Diode)		0.063		
	Case-to-Heatsink (per Module)		0.010		
M	Terminal Connection Torque, Screw M5	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

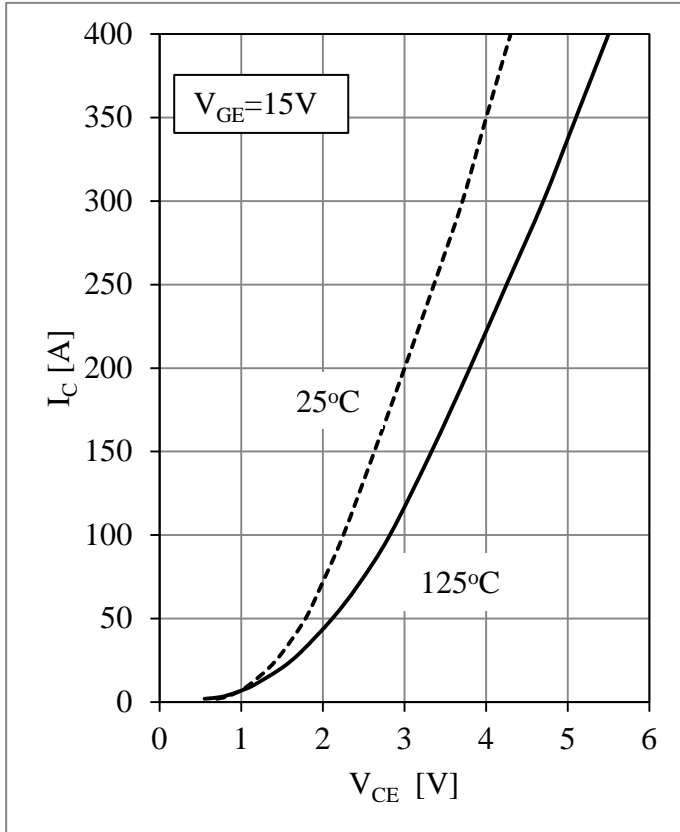


Fig 1. IGBT Output Characteristics

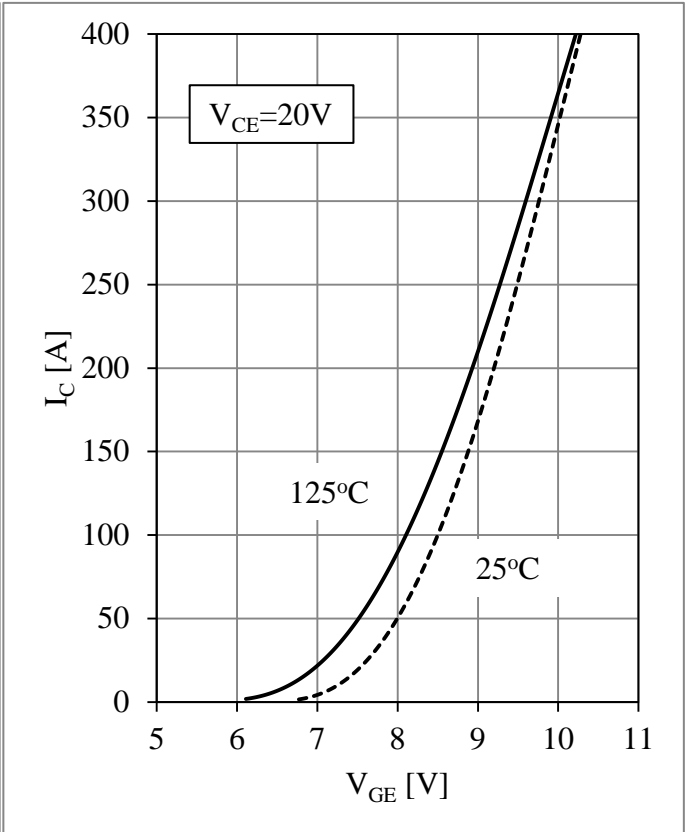


Fig 2. IGBT Transfer Characteristics

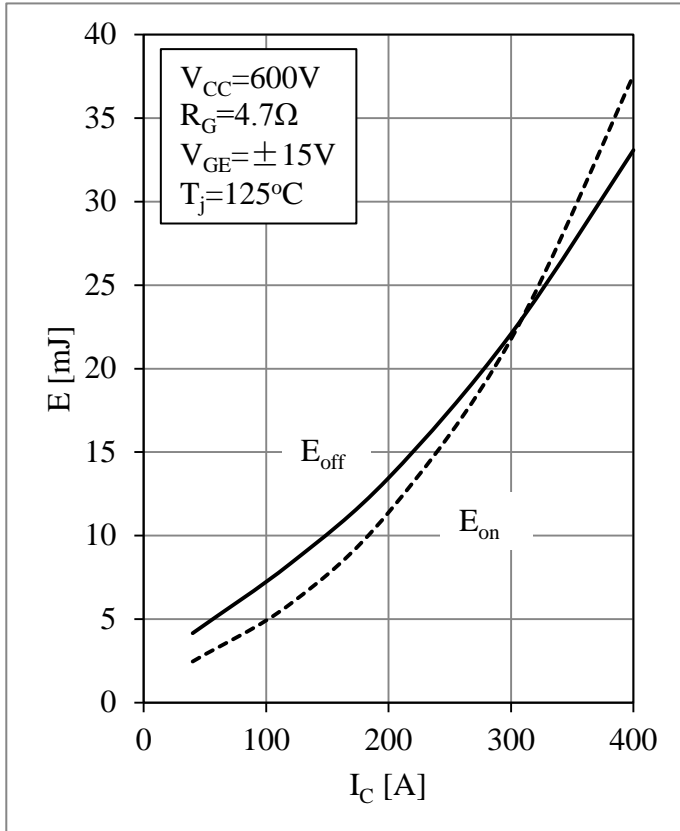


Fig 3. IGBT Switching Loss vs.  $I_C$

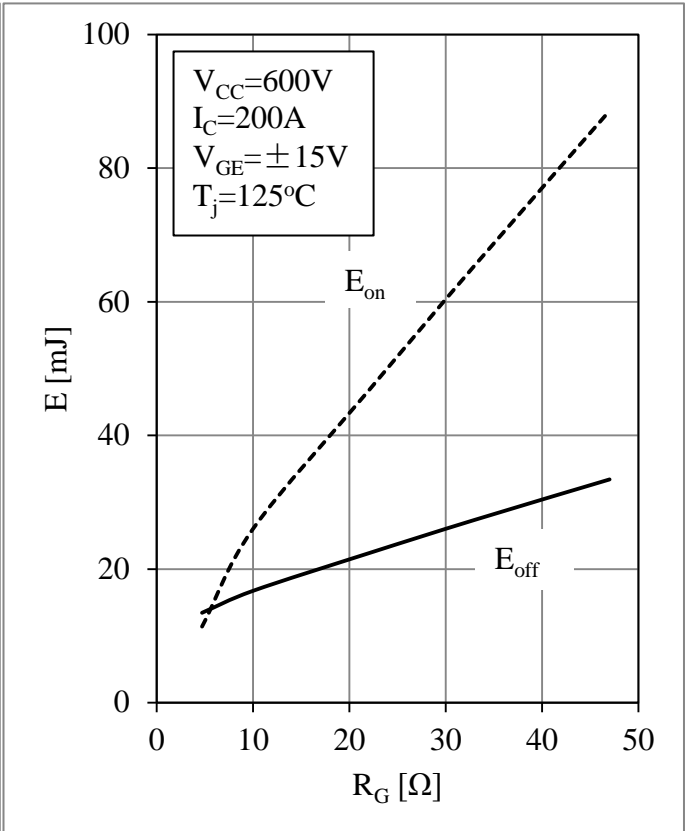


Fig 4. IGBT Switching Loss vs.  $R_G$

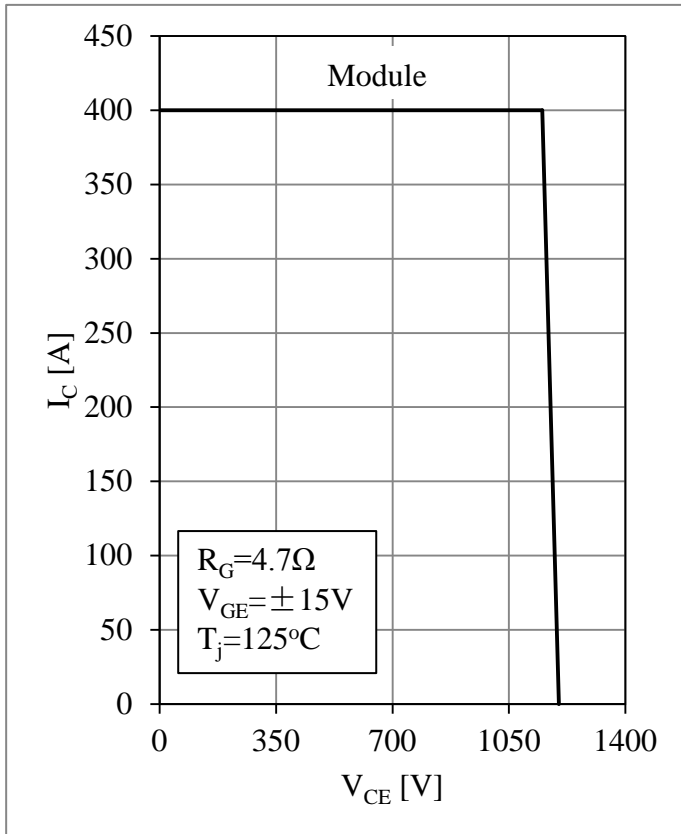


Fig 5. RBSOA

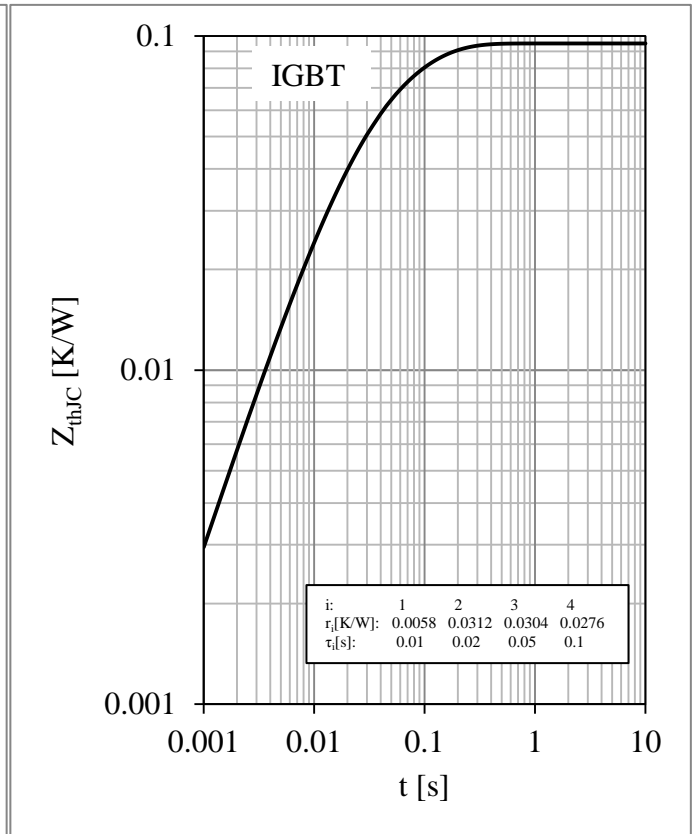


Fig 6. IGBT Transient Thermal Impedance

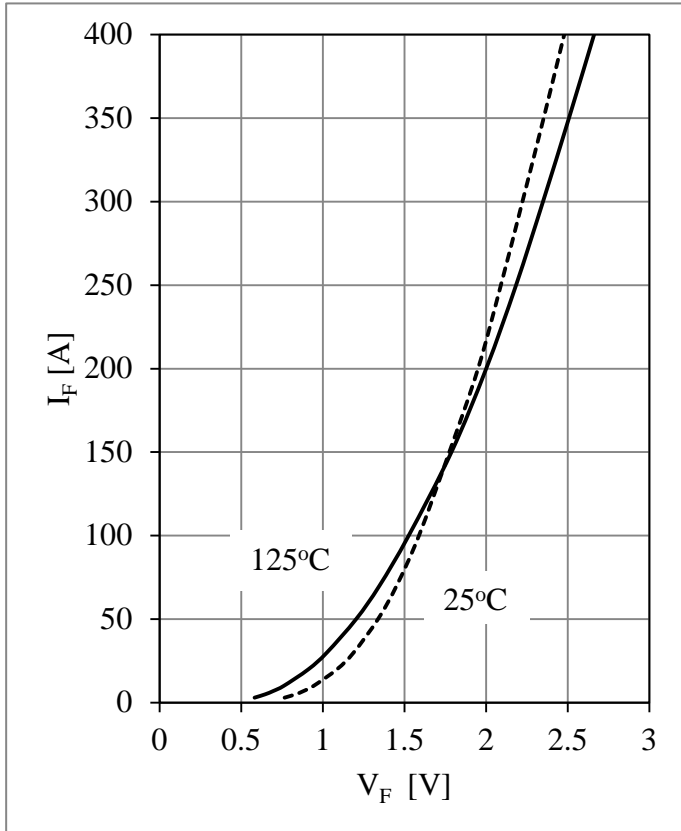


Fig 7. Diode Forward Characteristics

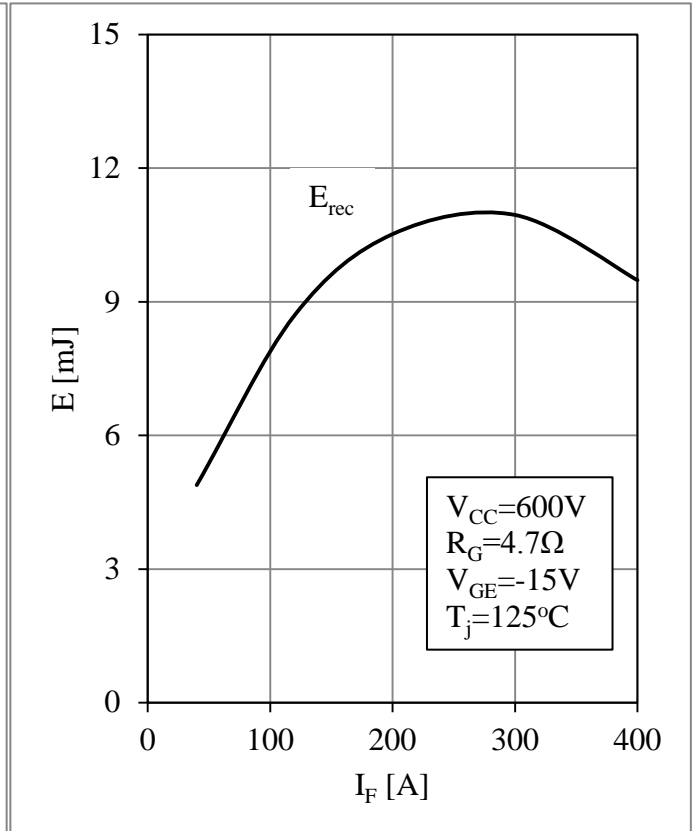


Fig 8. Diode Switching Loss vs.  $I_F$

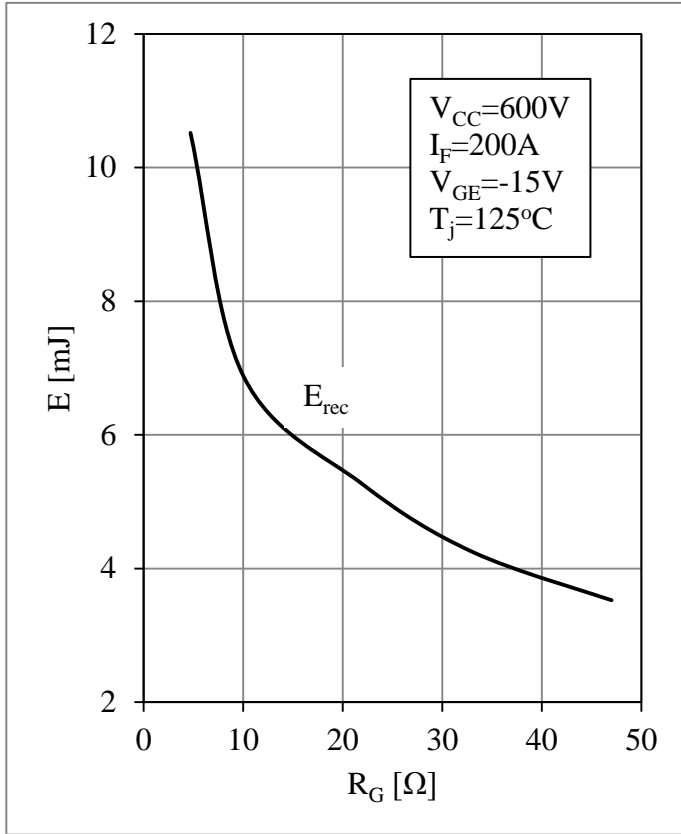


Fig 9. Diode Switching Loss vs.  $R_G$

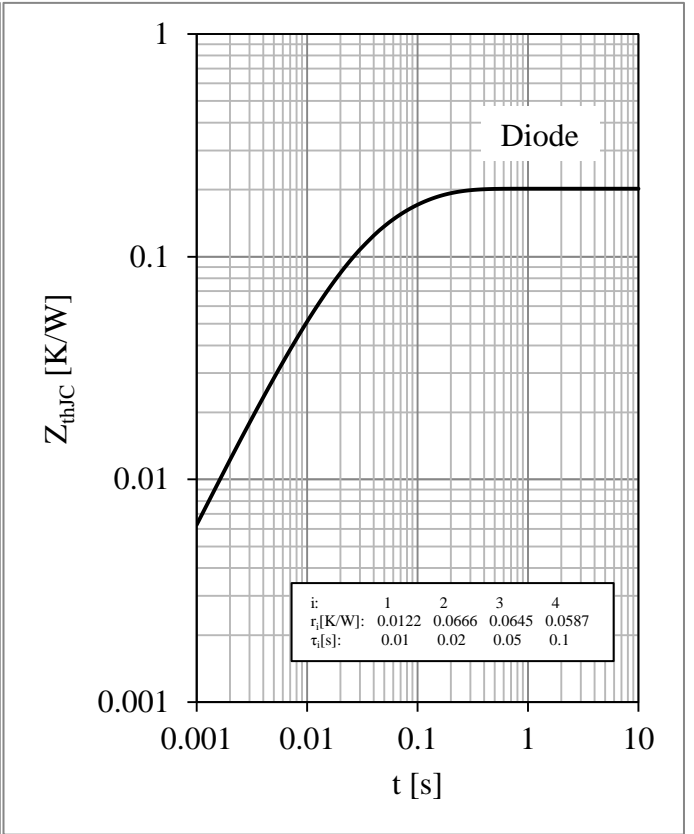
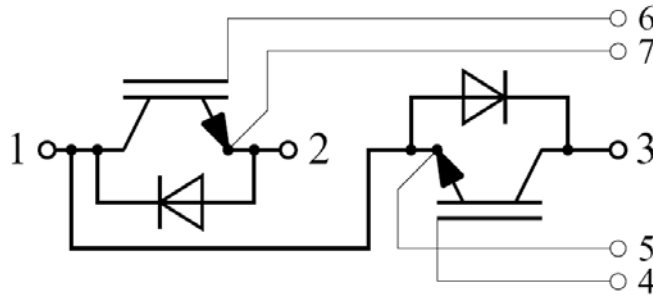


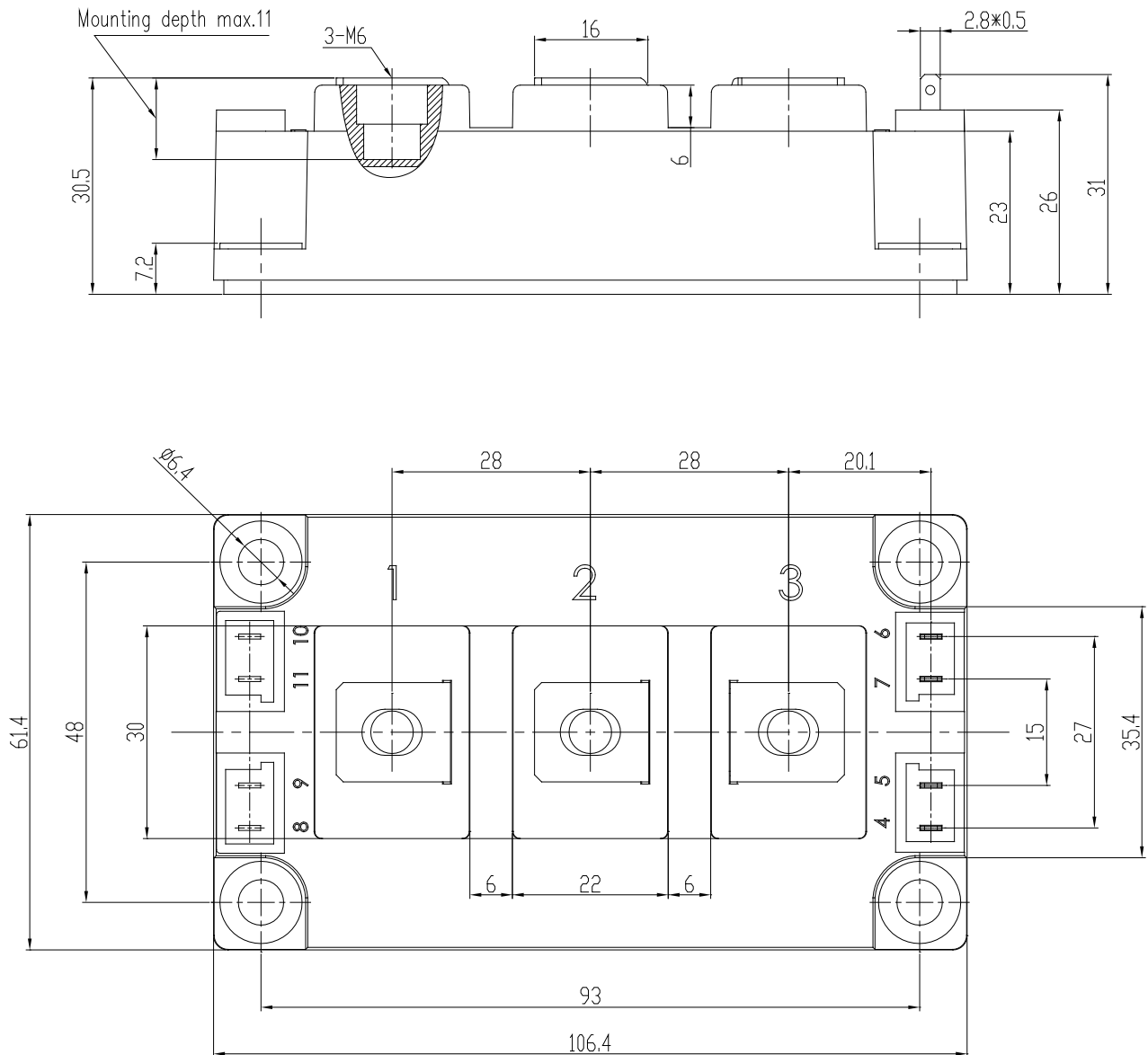
Fig 10. Diode Transient Thermal Impedance

### Circuit Schematic



### Package Dimensions

Dimensions in Millimeters





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